# TS5USBC41 デュアル 2:1 USB 2.0マルチプレクサ/デマルチプレクサ、またはシングルエンド・クロス・スイッチ、20V/24Vの過電圧保護搭載

## 1 特長

- 2.3V～5.5Vの電源電圧範囲
- 差動2:1または1:2スイッチ/マルチプレクサ、または柔軟なデュアル・シングルエンド・クロス・スイッチ
- 共通ピンで0V～20V (TS5USBC410)および24V (TS5USBC412)の過電圧保護(OVP)
- $V_{CC}$ = 0Vでの電源オフ保護
- 低い$R_{ON}$: 9Ω (最大値)
- 標準値1.1GHz (TS5USBC410)および1.2GHz (TS5USBC412)のBW
- $C_{ON}$容量2.7pF (TS5USBC410)および2.5pF (TS5USBC412)
- 低消費電力のディセーブル・モード
- 1.8V互換のロジック入力
- JESD 22を超えるESD保護
  - 人体モデル(HBM) 2000V
- TS5USBC410およびTS5USBC412: 標準温度範囲 0℃～70℃
- TS5USBC410IおよびTS5USBC412I: 工業用温度範囲 -40℃～85℃
- 小型のDSBGAパッケージ

## 2 アプリケーション

- モバイル
- PC/ノートPC
- タブレット
- USB Type-C™またはMicro-Bコネクタが使用される、あらゆる場所

## 3 概要

TS5USBC41は双方向、低消費電力のデュアル・ポート、高速、USB 2.0アナログ・スイッチで、USB Type-C™システム用の保護機能が内蔵されています。このデバイスは、デュアル2:1または1:2スイッチとして構成されます。USB Type-C™システムのUSB 2.0 D+/-ラインで使用するよう最適化されています。

TS5USBC41のI/Oピンの保護機能は、20V (TS5USBC410)または24V (TS5USBC412)までの電圧に耐えられ、自動シャットオフ回路により、スイッチの後方にあるシステム・コンポーネントを保護します。

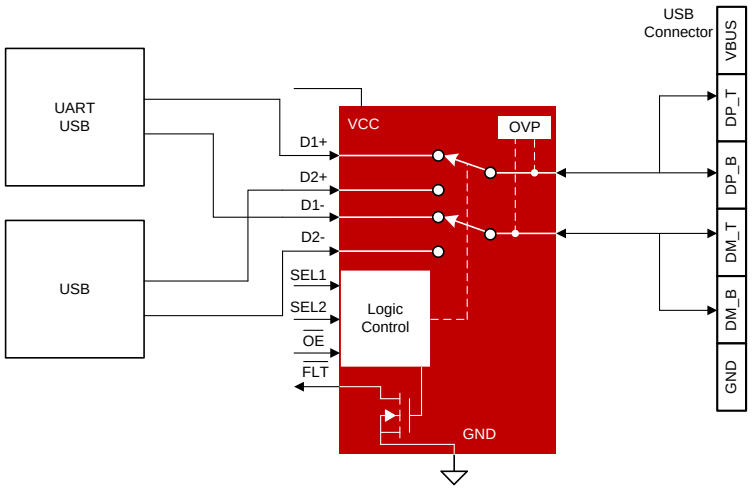
TS5USBC41は小型の12ピンDSBGAパッケージで供給され、モバイル・アプリケーションやスペースの制限されるアプリケーションにとって最適な選択肢となります。

**製品情報(1)**

| 型番 | パッケージ | 本体サイズ(公称) |
|---|---|---|
| TS5USBC410<br>TS5USBC410I<br>TS5USBC412<br>TS5USBC412I | DSBGA (12) | 1.638mm×1.238mm |

(1) 提供されているすべてのパッケージについては、巻末の注文情報を参照してください。

**概略回路図**




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# 目次

**1** 特長 ... 1
**2** アプリケーション ... 1
**3** 概要 ... 1
**4** 改訂履歴 ... 2
**5** **Pin Configuration and Functions** ... 3
**6** **Specifications** ... 4
6.1 Absolute Maximum Ratings ... 4
6.2 ESD Ratings ... 4
6.3 Recommended Operating Conditions ... 4
6.4 Thermal Information ... 5
6.5 Electrical Characteristics ... 5
6.6 Dynamic Characteristics ... 8
6.7 Timing Requirements ... 8
6.8 Typical Characteristics ... 9
**7** **Parameter Measurement Information** ... 10
**8** **Detailed Description** ... 14
8.1 Overview ... 14
8.2 Functional Block Diagram ... 14
8.3 Feature Description ... 15
8.4 Device Functional Modes ... 17
**9** **Application and Implementation** ... 18
9.1 Application Information ... 18
9.2 Typical Application ... 18
**10** **Power Supply Recommendations** ... 19
**11** **Layout** ... 20
11.1 Layout Guidelines ... 20
11.2 Layout Example ... 21
**12** デバイスおよびドキュメントのサポート ... 22
12.1 ドキュメントのサポート ... 22
12.2 ドキュメントの更新通知を受け取る方法 ... 22
12.3 コミュニティ・リソース ... 22
12.4 商標 ... 22
12.5 静電気放電に関する注意事項 ... 22
12.6 Glossary ... 22
**13** メカニカル、パッケージ、および注文情報 ... 22

## 4 改訂履歴

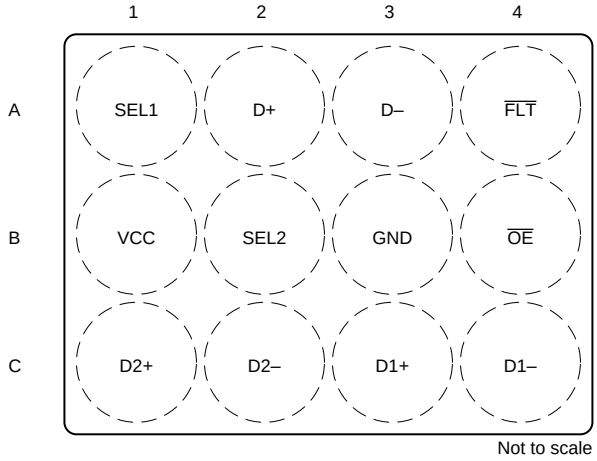
**Revision A (May 2018)** から **Revision B** に変更 **Page**

- デバイスのステータスを「*事前情報*」から「*量産データ*」に変更 ... 1


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# 5 Pin Configuration and Functions

**YFF Package**
**12-Pin DSBGA**
**Top View**




Not to scale

**Pin Functions**

| PIN | | I/O | DESCRIPTION |
|---|---|---|---|
| NO. | NAME | | |
| A1 | SEL1 | I | Switch select1. Refer to 表 1. |
| A2 | D+ | I/O | Data switch input (Differential +). |
| A3 | D– | I/O | Data switch input (Differential –) |
| A4 | $\overline{FLT}$ | O | Fault indicator output pin (Active low) - open drain |
| B1 | VCC | PWR | Supply Voltage |
| B2 | SEL2 | I | Switch select2. Refer to 表 1. |
| B3 | GND | GND | Ground |
| B4 | $\overline{OE}$ | I | Output enable (Active low). Refer to 表 1. |
| C1 | D2+ | I/O | Data switch output 2 (Differential +) |
| C2 | D2– | I/O | Data switch output 2 (Differential -) |
| C3 | D1+ | I/O | Data switch output 1 (Differential +) |
| C4 | D1– | I/O | Data switch output 1 (Differential -) |

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# 6 Specifications

## 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1) (2)

| | | MIN | MAX | UNIT |
|---|---|---|---|---|
| $V_{CC}$ | Supply voltage(3) | -0.5 | 6 | V |
| $V_{I/O}$ | Input/Output DC voltage (D+, D-) (TS5USBC412, TS5USBC412I)(3) | -0.5 | 28 | V |
| $V_{I/O}$ | Input/Output DC voltage (D+, D-) (TS5USBC410, TS5USBC410I)(3) | -0.5 | 24 | V |
| $V_{I/O}$ | Input/Output DC voltage (D1+/D1-, D2+/D2-)(3) | -0.5 | 6 | V |
| $V_I$ | Digital input voltage (SEL1, SEL2, $\overline{OE}$) | -0.5 | 6 | V |
| $V_O$ | Digital output voltage ($\overline{FLT}$) | -0.5 | 6 | V |
| $I_K$ | Input-output port diode current (D+, D-, D1+, D1-, D2+, D2-) when $V_{IN} < 0$ | -50 | | mA |
| $I_{IK}$ | Digital logic input clamp current (SEL1, SEL2, $\overline{OE}$) when $V_I < 0$ (3) | -50 | | mA |
| $I_{CC}$ | Continuous current through VCC | | 100 | mA |
| $I_{GND}$ | Continuous current through GND | -100 | | mA |
| $T_{stg}$ | Storage temperature | -65 | 150 | °C |

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. Theseare stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) The algebraic convention, whereby the most negative value is a minimum and the most positive value is a maximum.
(3) All voltages are with respect to ground, unless otherwisespecified.

## 6.2 ESD Ratings

| | | | VALUE | UNIT |
|---|---|---|---|---|
| $V_{(ESD)}$ | Electrostatic discharge | Human body model (HBM), per ANSI/ESDA/JEDEC JS-001(1) | ±2000 | V |
| | | Charged-device model (CDM), per JEDEC specification JESD22-C101(2) | ±1000 | |

(1) JEDEC document JEP155 states that 500-V HBM allows safemanufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safemanufacturing with a standard ESD control process.

## 6.3 Recommended Operating Conditions

| | | MIN | MAX | UNIT |
|---|---|---|---|---|
| $V_{CC}$ | Supply voltage | 2.3 | 5.5 | V |
| $V_{I/O}$ (D+, D-) | Analog input/output voltage (TS5USBC412, TS5USBC412I) | 0 | 24 | V |
| $V_{I/O}$ (D+, D-) | Analog input/output voltage (TS5USBC410, TS5USBC410I) | 0 | 20 | V |
| $V_{I/O}$ (D1, D1-, D2+, D2-) | Analog input/output voltage | 0 | 3.6 | V |
| $V_I$ | Digital input voltage (SEL1, SEL2, $\overline{OE}$) | 0 | 5.5 | V |
| $V_O$ | Digital output voltage ($\overline{FLT}$) | 0 | 5.5 | V |
| $I_{I/O}$ (D+, D-, D1+, D1-, D2+, D2-) | Analog input/output port continuous current | -50 | 50 | mA |
| $I_{OL}$ | Digital output current | | 3 | mA |
| $T_A$ | Operating free-air temperature (Standard) (TS5USBC410, TS5USBC412) | 0 | 70 | ºC |
| $T_A$ | Operating free-air temperature (Industrial) (TS5USBC410I, TS5USBC412I) | –40 | 85 | ºC |
| $T_J$ | Junction temperature | –40 | 125 | ºC |


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## 6.4 Thermal Information

| THERMAL METRIC (1) | | Device YFF 12 PINS | UNIT |
|---|---|---|---|
| $R_{\theta JA}$ | Junction-to-ambient thermal resistance | 91.8 | °C/W |
| $R_{\theta JC(top)}$ | Junction-to-case (top) thermal resistance | 0.8 | °C/W |
| $R_{\theta JB}$ | Junction-to-board thermal resistance | 22.8 | °C/W |
| $\psi_{JT}$ | Junction-to-top characterization parameter | 0.5 | °C/W |
| $\psi_{JB}$ | Junction-to-board characterization parameter | 23.0 | °C/W |

(1) For more information about traditional and new thermalmetrics, see the *Semiconductor and ICPackage Thermal Metrics* application report.

## 6.5 Electrical Characteristics

$T_A$ = –40°C to +85°C (Industrial), $T_A$ = 0℃ to 70℃ (Standard),$V_{CC}$ = 2.3 V to 5.5 V, GND = 0 V, Typical values are at $V_{CC}$ = 3.3 V, $T_A$ = 25°C, (unless otherwise noted)

| PARAMETER | | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|
| **POWER** | | | | | | |
| $I_{CC-ACTIVE}$ | Active supply current. | $\overline{OE}$ = 0 V<br>SEL1, SEL2 = 0 V, 1.8 V or $V_{CC}$<br>0 V < $V_{I/O}$ < 3.6 V | | 9 | 22 | µA |
| $I_{CC-OVP}$ | Supply current during OVP condition. | $\overline{OE}$ = 0 V<br>SEL1, SEL2 = 0 V, 1.8 V or $V_{CC}$<br>$V_{I/O}$ > $V_{POS_THLD}$ | | 10 | 35 | µA |
| $I_{CC_PD}$ | Standby powered down supply current | $\overline{OE}$ = 1.8 V or $V_{CC}$<br>SEL1 = 0 V, 1.8 V, or VCC<br>SEL2 = 0 V, 1.8 V, or VCC | | 2 | 6 | µA |
| **DC Characteristics** | | | | | | |
| $R_{ON}$ | ON-state resistance | $V_{I/O}$ = 0.4 V<br>$I_{SINK}$ = 8 mA<br>Refer to ON-State Resistance Figure | | 5.6 | 9 | Ω |
| $\Delta R_{ON}$ | ON-state resistance match between channels | $V_{I/O}$ = 0.4 V<br>$I_{SINK}$ = 8 mA<br>Refer to ON-State Resistance Figure | | 0.075 | 0.48 | Ω |
| $R_{ON\ (FLAT)}$ | ON-state resistance flatness | $V_{I/O}$ = 0 V to 0.4 V<br>$I_{SINK}$ = 8 mA<br>Refer to ON-State Resistance Figure | | 0.1 | 0.4 | Ω |
| $I_{OFF}$ | I/O pin OFF leakage current | OE = H<br>$V_{D\pm}$ = 0 V or 3.6 V<br>$V_{CC}$ = 2.3 V to 5.5 V<br>$V_{D1\pm}$or $V_{D2\pm}$ = 3.6 V or 0 V<br>Refer to Off Leakage Figure | -4 | 0.1 | 4 | µA |
| $I_{OFF-20V}$ | D1/D2+/- pin OFF leakage current during OVP scenario on D+/- | OE = H<br>$V_{D\pm}$ = 20-V<br>$V_{CC}$ = 2.3 V to 5.5 V<br>$V_{D1\pm}$ or $V_{D2\pm}$ = 0 V<br>Refer to Off Leakage Figure | -0.5 | | 0.5 | µA |
| $I_{OFF-20V-DP/N}$ | D+/- pin OFF leakage current during OVP scenario | OE = H<br>$V_{D\pm}$ = 20-V<br>$V_{CC}$ = 2.3 V to 5.5 V<br>$V_{D1\pm}$ or $V_{D2\pm}$ = 0 V<br>Refer to Off Leakage Figure | 140 | 150 | 180 | µA |

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## Electrical Characteristics (continued)

$T_A$ = –40°C to +85°C (Industrial), $T_A$ = 0℃ to 70℃ (Standard),$V_{CC}$ = 2.3 V to 5.5 V, GND = 0 V, Typical values are at $V_{CC}$ = 3.3 V, $T_A$ = 25°C, (unless otherwise noted)

| PARAMETER | | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|
| $I_{OFF-24V}$ | D1/D2 +/- pin OFF leakage current during OVP scenario on D+/-. | OE = H<br>$V_{D±}$ = 24-V<br>$V_{CC}$ = 2.3 V to 5.5 V<br>$V_{D1±}$ or $V_{D2±}$ = 0 V<br>Refer to Off Leakage Figure | -0.5 | | 0.5 | µA |
| $I_{OFF-24V-DPN}$ | D+/- pin OFF leakage current during OVP scenario. | OE = H<br>$V_{D±}$ = 0 V or 24-V<br>$V_{CC}$ = 2.3 V to 5.5 V<br>$V_{D1±}$ or $V_{D2±}$ = 0 V<br>Refer to Off Leakage Figure | 220 | 250 | 270 | µA |
| $I_{ON}$ | ON leakage current. | $V_{D±}$ = 0 V or 3.6 V<br>$V_{D1±}$ and $V_{D2+/-}$ = high-Z<br>Refer to On Leakage Figure | -5.5 | 0.25 | 7.5 | µA |
| **Digital Characteristics** | | | | | | |
| $V_{IH}$ | Input logic high | SEL1, SEL2, $\overline{OE}$ | 1.4 | | | V |
| $V_{IL}$ | Input logic low | SEL1, SEL2, $\overline{OE}$ | | | 0.5 | V |
| $V_{OL}$ | Output logic low | $\overline{FLT}$<br>$I_{OL}$ = 3 mA | | | 0.4 | V |
| $I_{IH}$ | Input high leakage current | SEL1, SEL2, $\overline{OE}$ = 1.8 V, $V_{CC}$ | -1 | 1 | 5 | µA |
| $I_{IL}$ | Input low leakage current | SEL1, SEL2, $\overline{OE}$ = 0 V | -1 | ±0.2 | 5 | µA |
| $R_{PD}$ | Internal pull-down resistor on digital input pins | | | 6 | | MΩ |
| $C_I$ | Digital input capacitance | SEL1, SEL2 = 0 V, 1.8 V or VCC<br>f = 1 MHz | | 4 | | pF |
| **Protection** | | | | | | |
| $V_{OVP_TH}$ | OVP positive threshold | | 4.4 | 4.8 | 5.2 | V |
| $V_{OVP_HYST}$ | OVP threshold hysteresis | | 125 | 250 | 440 | mV |
| $V_{CLAMP_V}$ | Maximum voltage to appear on D1± and D2± pins during OVP scenario (TS5USBC412, TS5USBC412I) | $V_{D±}$ = 0 to 24 V<br>$t_{RISE}$ and $t_{FALL}$(10% to 90 %) = 100 ns<br>$R_L$ = Open<br>Switch on or off<br>$\overline{OE}$ = 0 V | | | 11.2 | V |
| $V_{CLAMP_V}$ | Maximum voltage to appear on D1± and D2± pins during OVP scenario (TS5USBC412, TS5USBC412I) | $V_{D±}$ = 0 to 24 V<br>$t_{RISE}$ and $t_{FALL}$(10% to 90 %) = 100 ns<br>$R_L$ = 50Ω<br>Switch on or off<br>$\overline{OE}$ = 0 V | | | 10.8 | V |
| $V_{CLAMP_V}$ | Maximum voltage to appear on D1± and D2± pins during OVP scenario (TS5USBC410, TS5USBC410I) | $V_{D±}$ = 0 to 20 V<br>$t_{RISE}$ and $t_{FALL}$(10% to 90 %) = 100 ns<br>$R_L$ = Open<br>Switch on or off<br>$\overline{OE}$ = 0 V | | | 10.8 | V |
| $V_{CLAMP_V}$ | Maximum voltage to appear on D1± and D2± pins during OVP scenario (TS5USBC410, TS5USBC410I) | $V_{D±}$ = 0 to 20 V<br>$t_{RISE}$ and $t_{FALL}$(10% to 90 %) = 100 ns<br>$R_L$ = 50Ω<br>Switch on or off<br>$\overline{OE}$ = 0 V | | | 9.8 | V |


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## Electrical Characteristics (continued)

$T_A$ = –40°C to +85°C (Industrial), $T_A$ = 0℃ to 70℃ (Standard),$V_{CC}$ = 2.3 V to 5.5 V, GND = 0 V, Typical values are at $V_{CC}$ = 3.3 V, $T_A$ = 25°C, (unless otherwise noted)

| PARAMETER | | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|
| $V_{CLAMP_T}$ | Maximum OVP transient duration above 5 V (TS5USBC412, TS5USBC412I). | $V_{D\pm}$ = 0 to 24 V<br>$t_{RISE}$ and $t_{FALL}$(10% to 90 %) = 100 ns<br>$R_L$ = Open $C_L$ = 10pF<br>Switch on or off<br>$\overline{OE}$ = 0 V | | 75 | 100 | ns |
| $V_{CLAMP_T}$ | Maximum OVP transient duration above 5 V<br>(TS5USBC412, TS5USBC412I) | $V_{D\pm}$ = 0 to 24 V<br>$t_{RISE}$ and $t_{FALL}$(10% to 90 %) = 100 ns<br>$R_L$ = 50Ω $C_L$ = 10pF<br>Switch on or off<br>$\overline{OE}$ = 0 V | | 68 | 95 | ns |
| $V_{CLAMP_T}$ | Maximum OVP transient duration above 5 V<br>(TS5USBC410, TS5USBC410I) | $V_{D\pm}$ = 0 to 20 V<br>$t_{RISE}$ and $t_{FALL}$(10% to 90 %) = 100 ns<br>$R_L$ = Open $C_L$ = 10pF<br>Switch on or off<br>$\overline{OE}$ = 0 V | | 64 | 100 | ns |
| $V_{CLAMP_T}$ | Maximum OVP transient duration above 5 V<br>(TS5USBC410, TS5USBC410I) | $V_{D\pm}$ = 0 to 20 V<br>$t_{RISE}$ and $t_{FALL}$(10% to 90 %) = 100 ns<br>$R_L$ = 50Ω $C_L$ = 10pF<br>Switch on or off<br>$\overline{OE}$ = 0 V | | 55 | 95 | ns |
| $t_{EN_OVP}$ | OVP enable time | $R_{PU}$ = 10 kΩ to VCC ($\overline{FLT}$)<br>$C_L$ = 35 pF<br>Refer to OVP Timing Diagram Figure | | | 3 | µs |
| $t_{REC_OVP}$ | OVP recovery time | $R_{PU}$ = 10 kΩ to VCC ($\overline{FLT}$)<br>$C_L$ = 35 pF<br>Refer to OVP Timing Diagram Figure | | | 5 | µs |

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## 6.6 Dynamic Characteristics

$T_A$ = –40°C to +85°C (Industrial), $T_A$ = 0℃ to 70℃ (Standard),$V_{CC}$ = 2.3 V to 5.5V, GND = 0V, Typical values are at $V_{CC}$ = 3.3 V, $T_A$ = 25°C, (unless otherwise noted)

| PARAMETER | | TEST CONDITIONS | | MIN | TYP | MAX | UNIT |
|---|---|---|---|---|---|---|---|
| $C_{OFF}$ | D+, D- off capacitance | $\overline{V_{D+/-}}$ = 0 or 3.3 V,<br>$\overline{OE}$ = $V_{CC}$<br>f = 240 MHz | Switch OFF | 1.2 | 1.6 | 3.2 | pF |
| | D1+, D1-, D2+, D2- off capacitance | $\overline{V_{D+/-}}$ = 0 or 3.3 V,<br>$\overline{OE}$ = $V_{CC}$ or $\overline{OE}$ = 0V with SEL1, SEL2 (switch not selected)<br>f = 240 MHz | Switch OFF or not selected | 1.2 | 1.5 | 3.0 | pF |
| $C_{ON}$ | IO pins ON capacitance (TS5USBC412, TS5USBC412I) | $V_{D+/-}$ = 0 or 3.3 V,<br>f = 240 MHz | Switch ON | 2.0 | 2.5 | 3.9 | pF |
| $C_{ON}$ | IO pins ON capacitance (TS5USBC410, TS5USBC410I) | $V_{D+/-}$ = 0 or 3.3 V,<br>f = 240 MHz | Switch ON | 2.0 | 2.7 | 4 | pF |
| $O_{ISO}$ | Differential off isolation | RL = 50 Ω<br>CL = 5 pF<br>f = 100 kHz<br>Refer to Off Isolation Figure | Switch OFF | | -95 | | dB |
| | | RL = 50 Ω<br>CL = 5 pF<br>f = 240 MHz<br>Refer to Off Isolation Figure | Switch OFF | | -25 | | dB |
| $X_{TALK}$ | Channel to Channel crosstalk | RL = 50 Ω<br>CL = 5 pF<br>f = 100 kHz<br>Refer to Crosstalk Figure | Switch ON | | -90 | | dB |
| BW | Bandwidth (TS5USBC412, TS5USBC412I) | RL = 50 Ω; Refer to BW and Insertion Loss Figure | Switch ON | | 1.2 | | GHz |
| BW | Bandwidth (TS5USBC410, TS5USBC410I) | RL = 50 Ω; Refer to BW and Insertion Loss Figure | Switch ON | | 1.1 | | GHz |
| $I_{LOSS}$ | Insertion loss | RL = 50 Ω<br>f = 240 MHz; Refer to BW and Insertion Loss Figure | Switch ON | | -0.8 | | dB |

## 6.7 Timing Requirements

$T_A$ = –40°C to +85°C (Industrial), TA = 0℃ to 70℃ (Standard),$V_{CC}$ = 2.3 V to 5.5V, GND = 0V, Typical values are at$V_{CC}$ = 3.3 V, $T_A$ = 25°C, (unless otherwisenoted)

| PARAMETER | | TEST CONDITIONS | | MIN | NOM | MAX | UNIT |
|---|---|---|---|---|---|---|---|
| $t_{SWITCH}$ | Switching time between channels (SEL1, SEL2 to output) | $V_{D+/-}$ = 0.8 V<br>Refer to Tswitch Timing Figure | $R_L$ = 50 Ω,<br>$C_L$ = 5 pF,<br>$V_{CC}$ = 2.3 V to 5.5 V | | 0.8 | 2.5 | µs |
| $t_{ON}$ | Device turn on time ($\overline{OE}$ to output). | $V_{D+/-}$ = 0.8 V<br>Refer to Ton and Toff Figure | | | 84 | 250 | µs |
| $t_{OFF}$ | Device turn off time ($\overline{OE}$ to output) | $V_{D+/-}$ = 0.8 V<br>Refer to Ton and Toff Figure | | | 0.75 | 1 | µs |
| $t_{SK(P)}$ | Skew of opposite transitions of same output (between D+ and D-). | $V_{D+/-}$ = 0.4 V<br>Refer to Tsk Figure | $R_L$ = 50 Ω,<br>$C_L$ = 1 pF,<br>$V_{CC}$ = 2.3 V to 5.5 V | | 11 | 50 | ps |
| $t_{PD}$ | Propagation delay. | f - 240 MHz<br>$V_{D+/-}$ = 0.4 V<br>Refer to Tpd Figure | $R_L$ = 50 Ω,<br>$C_L$ = 5 pF,<br>$V_{CC}$ = 2.3 V to 5.5 V | | 150 | 230 | ps |


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## 6.8 Typical Characteristics

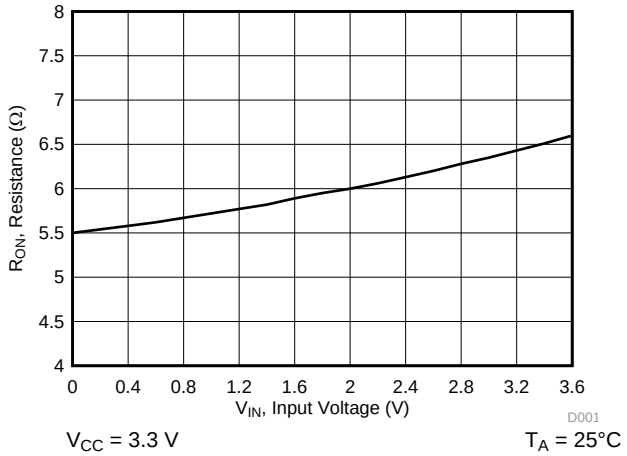



**図 1. ON-Resistance vs Input Voltage**

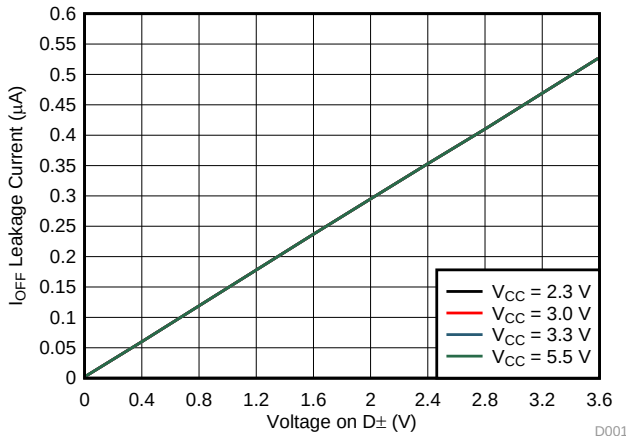



**図 2. $I_{OFF}$ Leakage Current vs Voltage on D±**

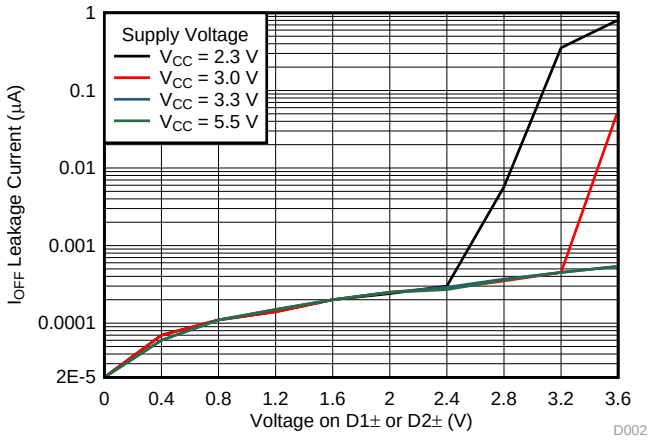



**図 3. $I_{OFF}$ Leakage Current vs Voltage on D1± or D2±**

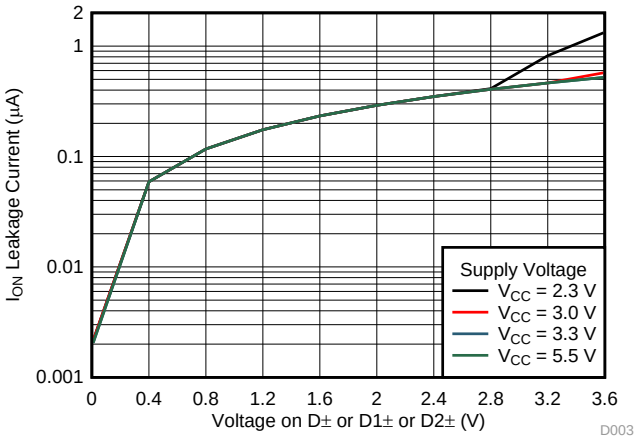
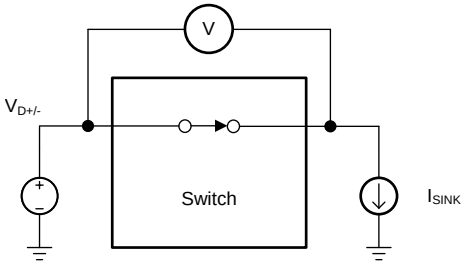



**図 4. $I_{ON}$ Leakage Current vs Voltage on D± or D1± or D2±**

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# 7 Parameter Measurement Information




Channel ON, $R_{ON} = V/I_{SINK}$

**図 5. ON-State Resistance ($R_{ON}$)**

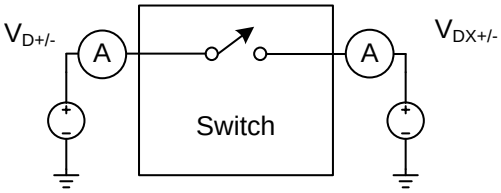



**図 6. Off Leakage**

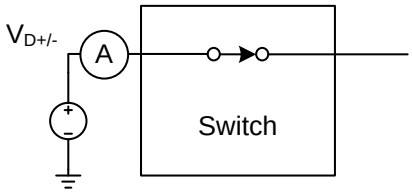
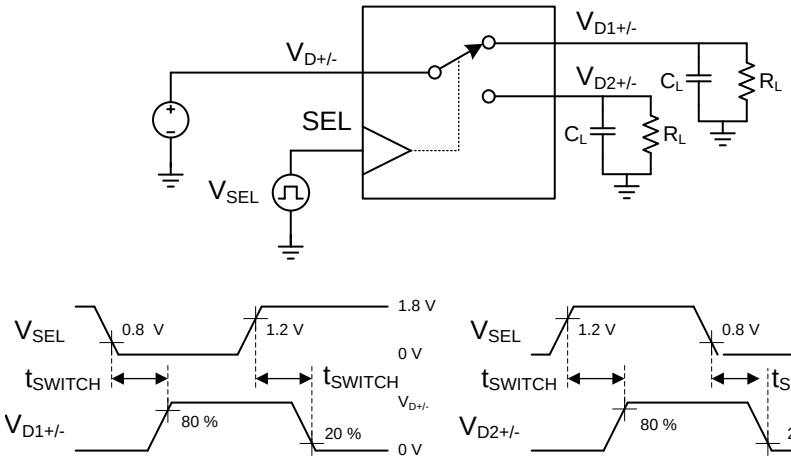



**図 7. On Leakage**



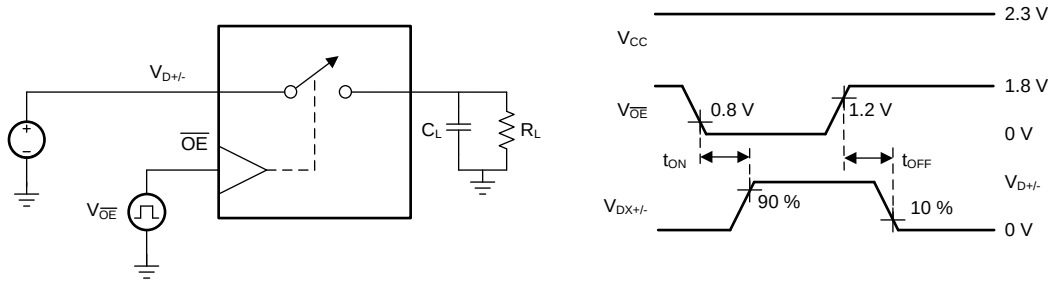

(1) All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, $Z_O$ = 50 Ω, $t_r$ < 500 ps, $t_f$ < 500 ps.

(2) $C_L$ includes probe and jig capacitance.

**図 8. $t_{SWITCH}$ Timing**


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## Parameter Measurement Information (continued)




(1) All input pulses are supplied by generators having the following characteristics: PRR = 10 MHz, $Z_O$ = 50 Ω, $t_r$ < 500 ps, $t_f$ < 500 ps.

(2) $C_L$ includes probe and jig capacitance.

**図 9. $t_{ON}$, $t_{OFF}$ for $\overline{OE}$**

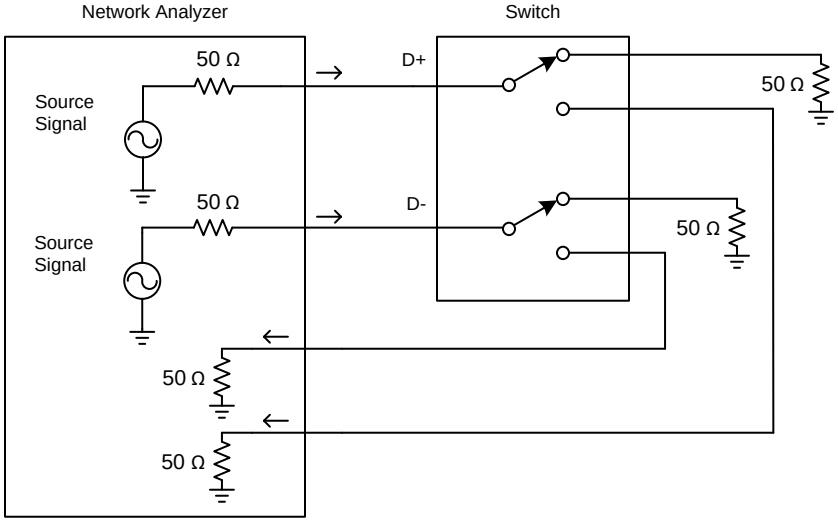



**図 10. Off Isolation**

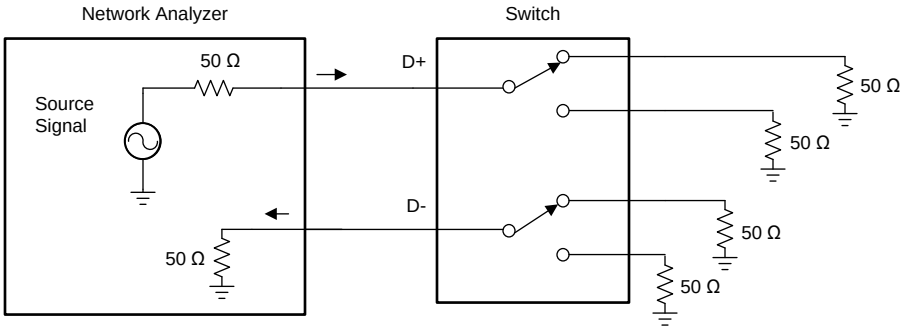



**図 11. Cross Talk**

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## Parameter Measurement Information (continued)

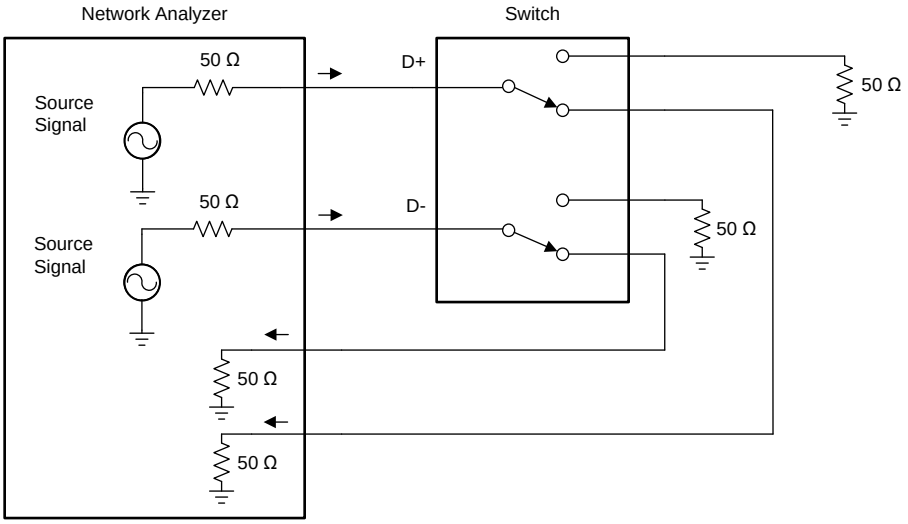



**図 12. BW and Insertion Loss**

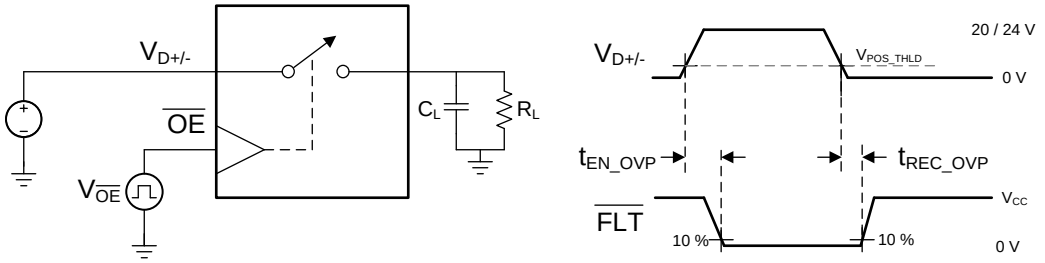
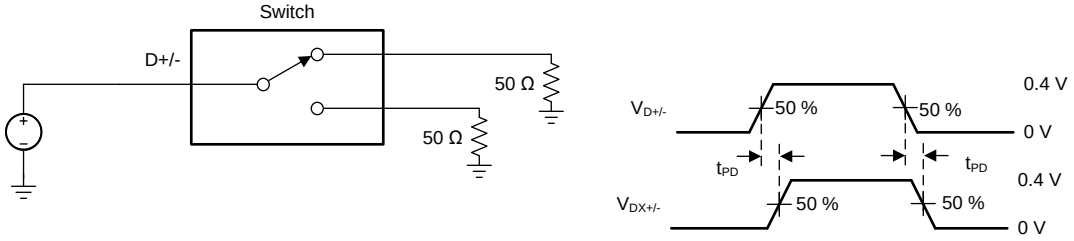



**図 13. $t_{EN_OVP}$ and $t_{DIS_OVP}$ Timing Diagram**



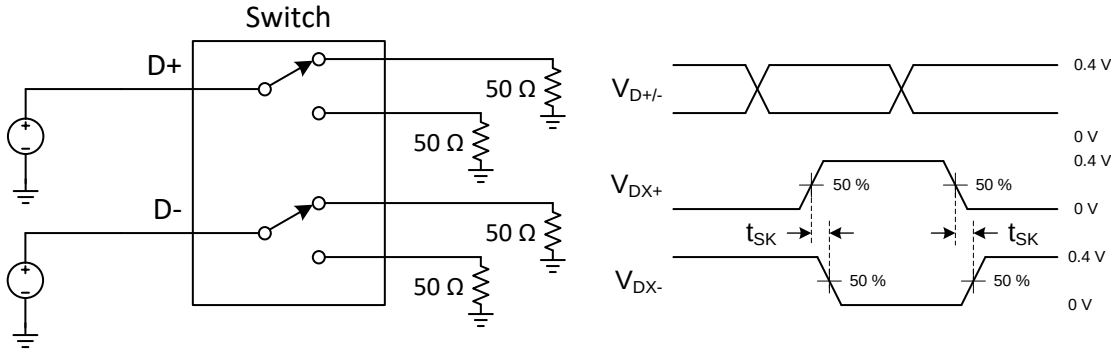

(1) All input pulses are supplied by generators having the following characteristics: PRR = 240 MHz, $Z_O$ = 50 Ω, $t_r$ < 500 ps, $t_f$ < 500 ps.

(2) $C_L$ includes probe and jig capacitance.

**図 14. $t_{PD}$**


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## Parameter Measurement Information (continued)




(1) All input pulses are supplied by generators having the following characteristics: PRR ≤ 10 MHz, $Z_O$ = 50 Ω, $t_r$ < 500 ps, $t_f$ < 500 ps.

(2) $C_L$ includes probe and jig capacitance.

**図 15. $t_{SK}$**

# 8 Detailed Description

## 8.1 Overview

The TS5USBC41 is a bidirectional low-power dual port, high-speed, USB 2.0 analog switch with integrated protection for USB Type-C systems. The device is configured as a dual 2:1 or 1:2 switch and is optimized for handling the USB 2.0 D+/- lines in a USB Type-C system as shown in 図 16.

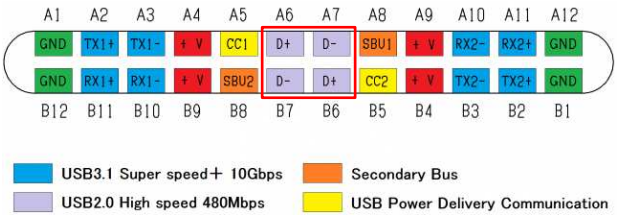
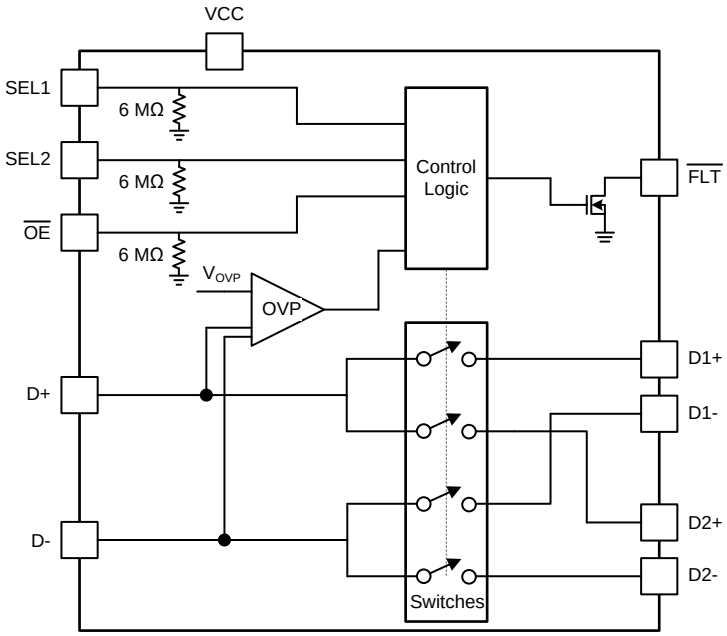



**図 16. USB Type-C Connector Pinout**

The TS5USBC41 also works in traditional USB systems that need protection from fault conditions such as automotive and applications that require higher voltage charging. The device maintains excellent signal integrity through the optimization of both $R_{ON}$ and BW while protecting the system with 20 V (TS5USBC410) and 24 V (TS5USBC412) OVP protection. The OVP implementation is designed to protect sensitive system components behind the switch that cannot survive a fault condition where VBUS is shorted to the D+ and D- pins on the connector.

## 8.2 Functional Block Diagram





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## 8.3 Feature Description

### 8.3.1 Powered-off Protection

When the TS5USBC41 is powered off the I/Os of the device remain in a high-Z state. The crosstalk, off-isolation, and leakage remain within the *Electrical Specifications*.

This prevents errant voltages from reaching the rest of the system and maintains isolation when the system is powering up.

### 8.3.2 Overvoltage Protection

The OVP of the TS5USBC41 is designed to protect the system from D+/- shorts to VBUS at the USB and USB Type-C connector. 図 17 depicts a moisture short that would cause high voltage (20 V for TS5USBC410 or 20 V for TS5USBC412) to appear on an existing USB solution that could pass through the device and damage components behind the device.

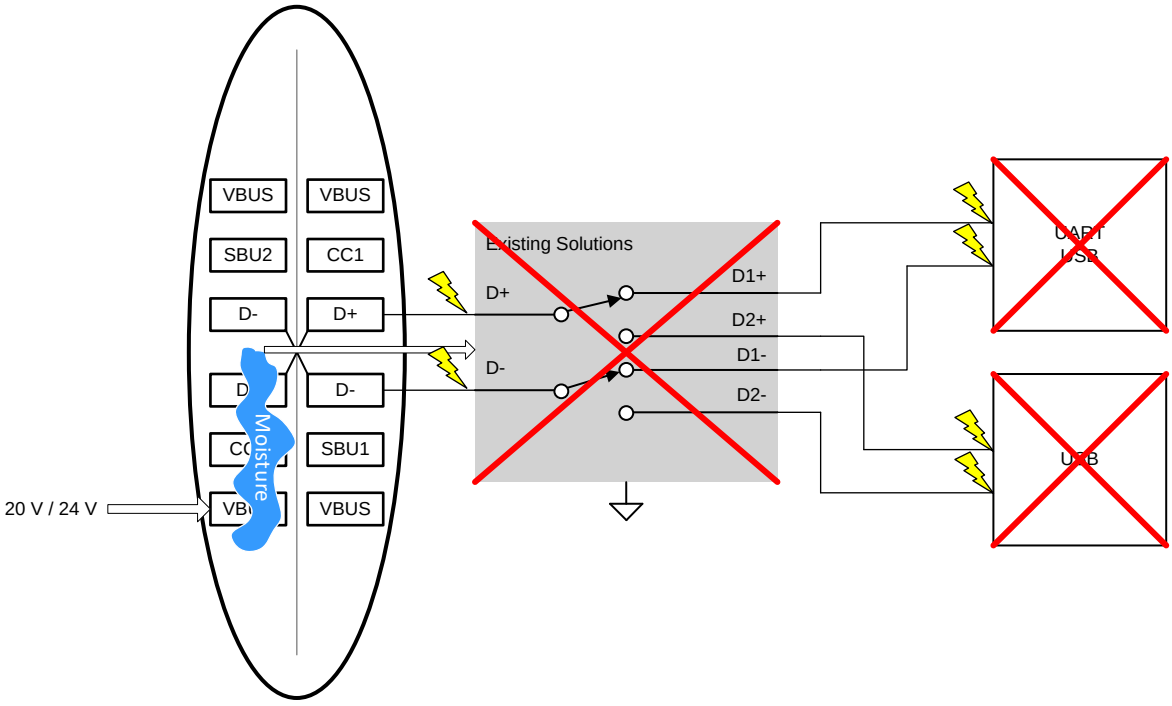



**図 17. Existing Solution Being Damaged by a Short**

## Feature Description (continued)

The TS5USBC41 will open the switches and protect the rest of the system by blocking the 20 V / 24 V as depicted in 図 18.

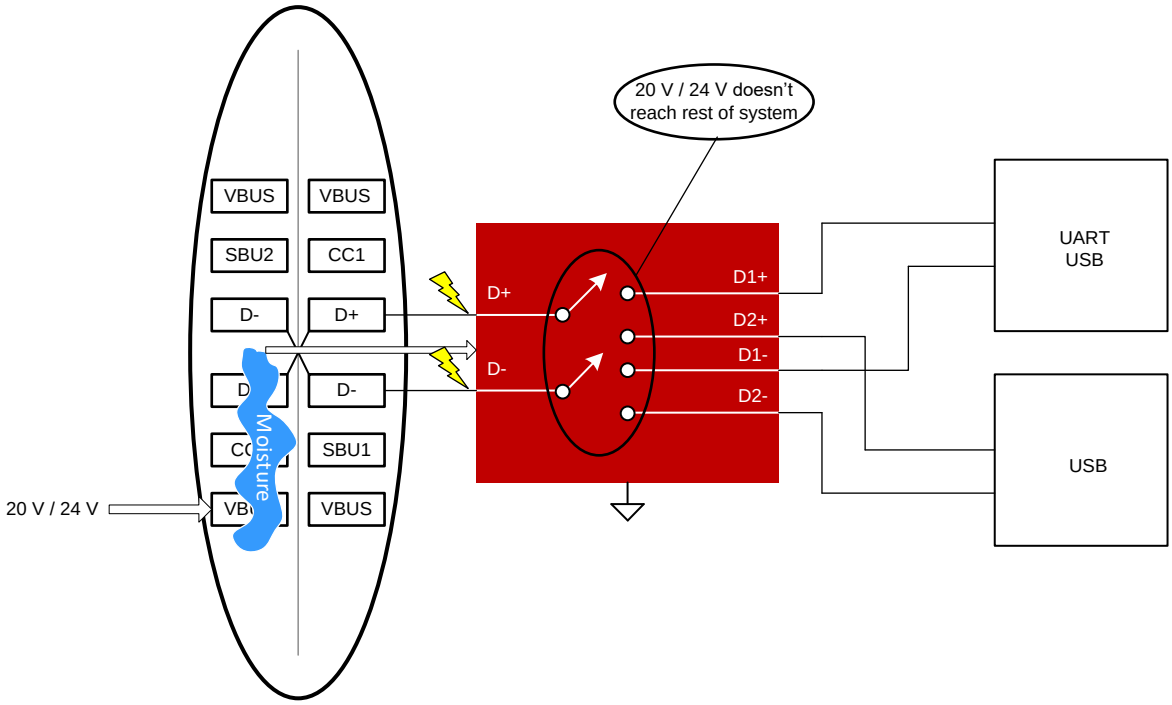



図 18. Protecting During a 20-V / 24-V Short

図 19 is a waveform showing the voltage on the pins during an over-voltage scenario.

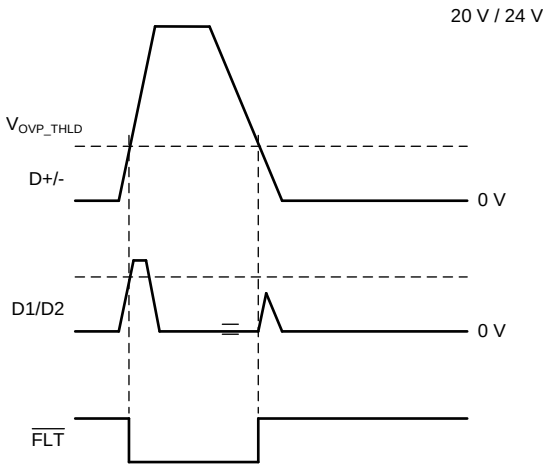



図 19. Overvoltage Protection Waveform


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## 8.4 Device Functional Modes

### 8.4.1 Pin Functions

**表 1. Function Table**

| $\overline{OE}$ | SEL1 | SEL2 | D- Connection | D+ Connection |
|---|---|---|---|---|
| H | X | X | High-Z | High-Z |
| L | L | L | D- to D1- | D+ to D1+ |
| L | L | H | D- to D1- | D+ to D2+ |
| L | H | L | D- to D2- | D+ to D1+ |
| L | H | H | D- to D2- | D+ to D2+ |

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# 9 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

## 9.1 Application Information

There are many USB applications in which the USB hubs or controllers have a limited number of USB I/Os or need to route signals from a single USB connector. The TS5USBC41 solution can effectively expand the limited USB I/Os by switching between multiple USB buses to interface them to a single USB hub or controller or route signals from on connector to two different locations. With independent control of the two switches using SEL1 and SEL2, TS5USBC41 can be used to cross switch single ended signals.

## 9.2 Typical Application

TS5USBC41 USB/UART switch. The TS5USBC41 is used to switch signals between the USB path, which goes to the baseband or application processor, or the UART path, which goes to debug port. The TS5USBC41 has internal 6-MΩ pull-down resistors on SEL1, SEL2, and $\overline{OE}$. The pull-down on SEL1 and SEL2 pins ensure the D1+/D1- channel is selected by default. The pull-down on $\overline{OE}$ enables the switch when power is applied.

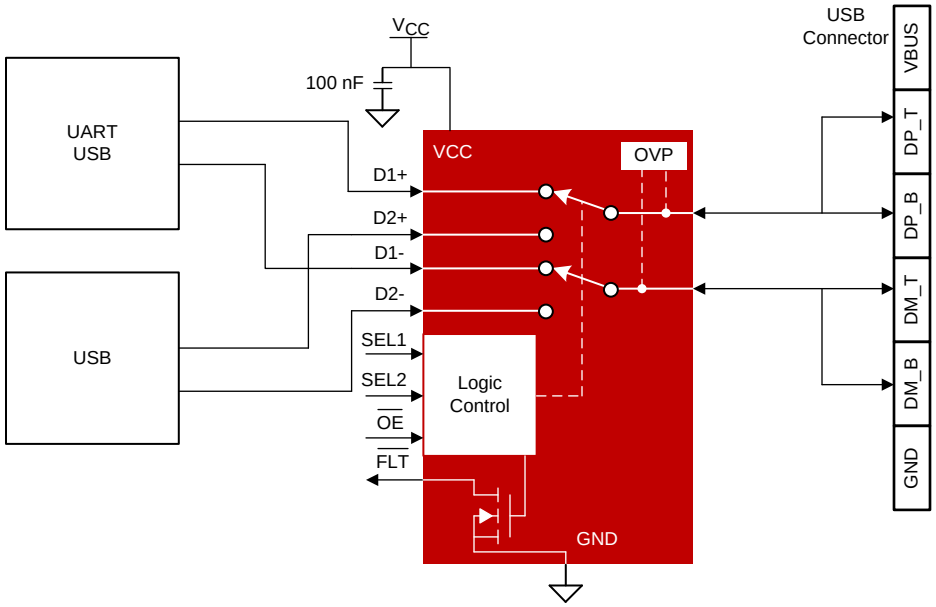



**図 20. Typical Application**

### 9.2.1 Design Requirements

Design requirements of USB 1.0,1.1, and 2.0 standards must be followed. The TS5USBC41 has internal 6-MΩ pulldown resistors on SEL1, SEL2, and $\overline{OE}$, so no external resistors are required on the logic pins. The internal pull-down resistor on SEL1 and SEL2 pins ensures the D1+ and D1- channels are selected by default. The internal pull-down resistor on $\overline{OE}$ enables the switch when power is applied to VCC.

### 9.2.2 Detailed Design Procedure

The TS5USBC41 can be properly operated without any external components. However, TI recommends that unused pins must be connected to ground through a 50-Ω resistor to prevent signal reflections back into the device. TI does recommend a 100-nF bypass capacitor placed close to TS5USBC41 VCC pin.


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## Typical Application (continued)

### 9.2.3 Application Curves

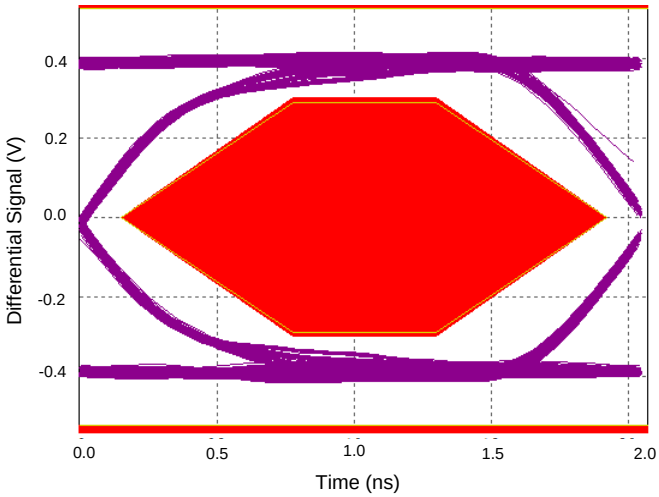



図 21. High Speed Eye Diagram With TS5USBC41

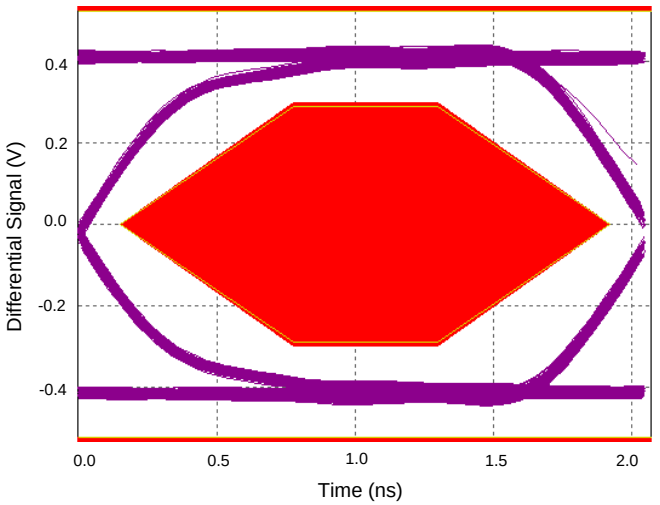



図 22. High Speed Eye Diagram Without TS5USBC41

## 10 Power Supply Recommendations

Power to the device is supplied through the VCC pin and must follow the USB 1.0, 1.1, and 2.0 standards. TI recommends placing a 100 nF bypass capacitor as close to the supply pin VCC as possible to help smooth out lower frequency noise to provide better load regulation across the frequency spectrum.

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# 11 Layout

## 11.1 Layout Guidelines

1. Place supply bypass capacitors as close to VCC pin as possible and avoid placing the bypass caps near the D± traces.
2. The high-speed D± must match and be no more than 4 inches long; otherwise, the eye diagram performance may be degraded. A high-speed USB connection is made through a shielded, twisted pair cable with a differential characteristic impedance. In layout, the impedance of D+ and D– traces must match the cable characteristic differential impedance for optimal performance.
3. Route the high-speed USB signals using a minimum of vias and corners which reduces signal reflections and impedance changes. When a via must be used, increase the clearance size around it to minimize its capacitance. Each via introduces discontinuities in the signal's transmission line and increases the chance of picking up interference from the other layers of the board. Be careful when designing test points on twisted pair lines; through-hole pins are not recommended.
4. When it becomes necessary to turn 90°, use two 45° turns or an arc instead of making a single 90° turn. This reduces reflections on the signal traces by minimizing impedance discontinuities.
5. Do not route USB traces under or near crystals, oscillators, clock signal generators, switching regulators, mounting holes, magnetic devices or ICs that use or duplicate clock signals.
6. Avoid stubs on the high-speed USB signals due to signal reflections. If a stub is unavoidable, then the stub must be less than 200 mm.
7. Route all high-speed USB signal traces over continuous GND planes, with no interruptions.
8. Avoid crossing over anti-etch, commonly found with plane splits.
9. Due to high frequencies associated with the USB, a printed circuit board with at least four layers is recommended; two signal layers separated by a ground and power layer as shown in 図 23.

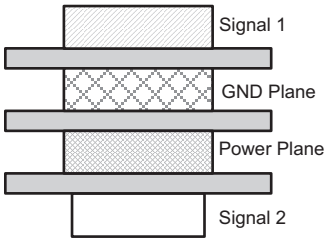



**図 23. Four-Layer Board Stack-Up**

The majority of signal traces must run on a single layer, preferably Signal 1. Immediately next to this layer must be the GND plane, which is solid with no cuts. Avoid running signal traces across a split in the ground or power plane. When running across split planes is unavoidable, sufficient decoupling must be used. Minimizing the number of signal vias reduces EMI by reducing inductance at high frequencies.


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## 11.2 Layout Example

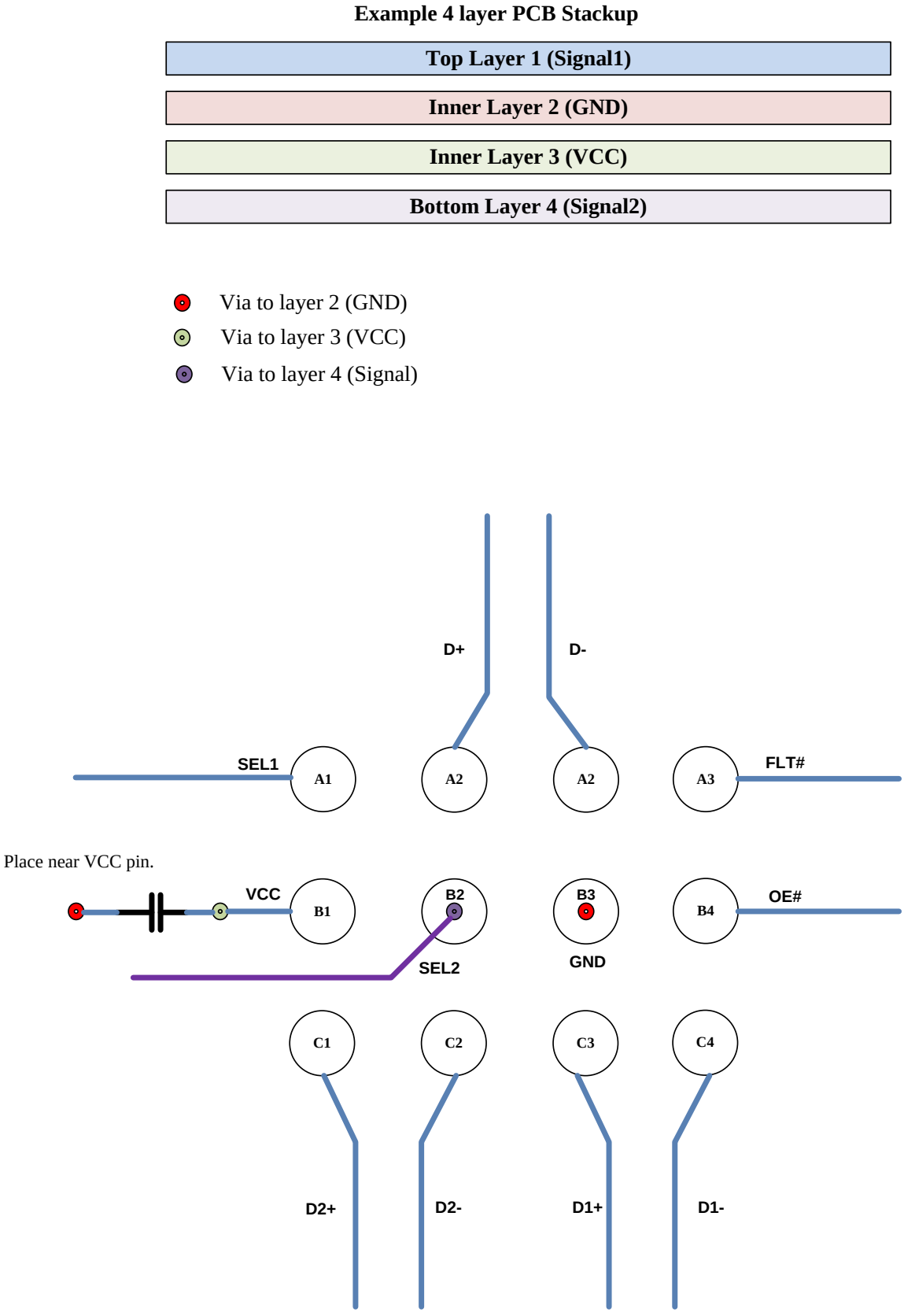



**図 24. Layout Example**

# 12 デバイスおよびドキュメントのサポート

## 12.1 ドキュメントのサポート

### 12.1.1 関連資料

関連資料については、以下を参照してください。

- *『USB 2.0基板の設計およびレイアウトのガイドライン』*
- *『高速レイアウト・ガイドライン』アプリケーション・レポート*
- *『高速インターフェイスのレイアウト・ガイドライン』*

## 12.2 ドキュメントの更新通知を受け取る方法

ドキュメントの更新についての通知を受け取るには、ti.comのデバイス製品フォルダを開いてください。右上の隅にある「*通知を受け取る*」をクリックして登録すると、変更されたすべての製品情報に関するダイジェストを毎週受け取れます。変更の詳細については、修正されたドキュメントに含まれている改訂履歴をご覧ください。

## 12.3 コミュニティ・リソース

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

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**設計サポート** ***TIの設計サポート*** **役に立つE2Eフォーラムや、設計サポート・ツールをすばやく見つけることができます。技術サポート用の連絡先情報も参照できます。**

## 12.4 商標

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USB Type-C is a trademark of USB Implementers Forum.
All other trademarks are the property of their respective owners.

## 12.5 静電気放電に関する注意事項

すべての集積回路は、適切なESD保護方法を用いて、取扱いと保存を行うようにして下さい。

静電気放電はわずかな性能の低下から完全なデバイスの故障に至るまで、様々な損傷を与えます。高精度の集積回路は、損傷に対して敏感であり、極めてわずかなパラメータの変化により、デバイスに規定された仕様に適合しなくなる場合があります。

## 12.6 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

# 13 メカニカル、パッケージ、および注文情報

以降のページには、メカニカル、パッケージ、および注文に関する情報が記載されています。この情報は、そのデバイスについて利用可能な最新のデータです。このデータは予告なく変更されることがあり、ドキュメントが改訂される場合もあります。本データシートのブラウザ版を使用されている場合は、画面左側の説明をご覧ください。


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## PACKAGING INFORMATION

| Orderable part number | Status (1) | Material type (2) | Package \| Pins | Package qty \| Carrier | RoHS (3) | Lead finish/ Ball material (4) | MSL rating/ Peak reflow (5) | Op temp (°C) | Part marking (6) |
|---|---|---|---|---|---|---|---|---|---|
| TS5USBC410IYFFR | Active | Production | DSBGA (YFF) \| 12 | 3000 \| LARGE T&R | Yes | SNAGCU | Level-1-260C-UNLIM | -40 to 85 | TU41 |
| TS5USBC410IYFFR.A | Active | Production | DSBGA (YFF) \| 12 | 3000 \| LARGE T&R | Yes | SNAGCU | Level-1-260C-UNLIM | -40 to 85 | TU41 |
| TS5USBC410IYFFT | Active | Production | DSBGA (YFF) \| 12 | 250 \| SMALL T&R | Yes | SNAGCU | Level-1-260C-UNLIM | -40 to 85 | TU41 |
| TS5USBC410IYFFT.A | Active | Production | DSBGA (YFF) \| 12 | 250 \| SMALL T&R | Yes | SNAGCU | Level-1-260C-UNLIM | -40 to 85 | TU41 |
| TS5USBC410YFFR | Active | Production | DSBGA (YFF) \| 12 | 3000 \| LARGE T&R | Yes | SNAGCU | Level-1-260C-UNLIM | 0 to 70 | TU41 |
| TS5USBC410YFFR.A | Active | Production | DSBGA (YFF) \| 12 | 3000 \| LARGE T&R | Yes | SNAGCU | Level-1-260C-UNLIM | 0 to 70 | TU41 |
| TS5USBC410YFFT | Active | Production | DSBGA (YFF) \| 12 | 250 \| SMALL T&R | Yes | SNAGCU | Level-1-260C-UNLIM | 0 to 70 | TU41 |
| TS5USBC410YFFT.A | Active | Production | DSBGA (YFF) \| 12 | 250 \| SMALL T&R | Yes | SNAGCU | Level-1-260C-UNLIM | 0 to 70 | TU41 |
| TS5USBC412IYFFR | Active | Production | DSBGA (YFF) \| 12 | 3000 \| LARGE T&R | Yes | SNAGCU | Level-1-260C-UNLIM | -40 to 85 | TU41 |
| TS5USBC412IYFFR.A | Active | Production | DSBGA (YFF) \| 12 | 3000 \| LARGE T&R | Yes | SNAGCU | Level-1-260C-UNLIM | -40 to 85 | TU41 |
| TS5USBC412IYFFT | Active | Production | DSBGA (YFF) \| 12 | 250 \| SMALL T&R | Yes | SNAGCU | Level-1-260C-UNLIM | -40 to 85 | TU41 |
| TS5USBC412IYFFT.A | Active | Production | DSBGA (YFF) \| 12 | 250 \| SMALL T&R | Yes | SNAGCU | Level-1-260C-UNLIM | -40 to 85 | TU41 |
| TS5USBC412YFFR | Active | Production | DSBGA (YFF) \| 12 | 3000 \| LARGE T&R | Yes | SNAGCU | Level-1-260C-UNLIM | 0 to 70 | TU41 |
| TS5USBC412YFFR.A | Active | Production | DSBGA (YFF) \| 12 | 3000 \| LARGE T&R | Yes | SNAGCU | Level-1-260C-UNLIM | 0 to 70 | TU41 |
| TS5USBC412YFFT | Active | Production | DSBGA (YFF) \| 12 | 250 \| SMALL T&R | Yes | SNAGCU | Level-1-260C-UNLIM | 0 to 70 | TU41 |
| TS5USBC412YFFT.A | Active | Production | DSBGA (YFF) \| 12 | 250 \| SMALL T&R | Yes | SNAGCU | Level-1-260C-UNLIM | 0 to 70 | TU41 |

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

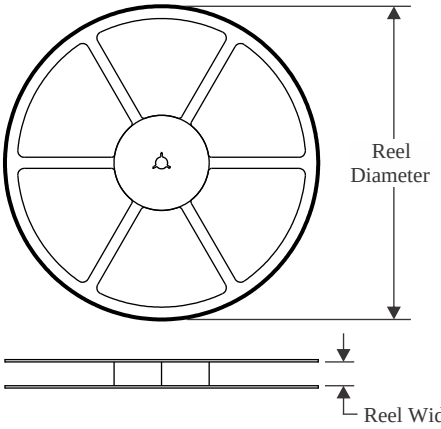
Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

**Important Information and Disclaimer:**The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

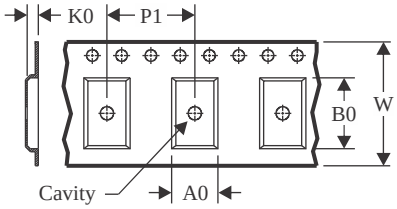
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

## TAPE AND REEL INFORMATION

**REEL DIMENSIONS**

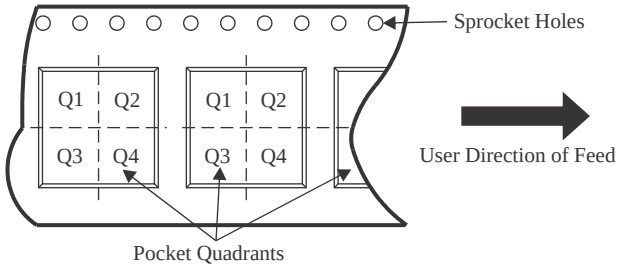



**TAPE DIMENSIONS**




| | |
|---|---|
| A0 | Dimension designed to accommodate the component width |
| B0 | Dimension designed to accommodate the component length |
| K0 | Dimension designed to accommodate the component thickness |
| W | Overall width of the carrier tape |
| P1 | Pitch between successive cavity centers |

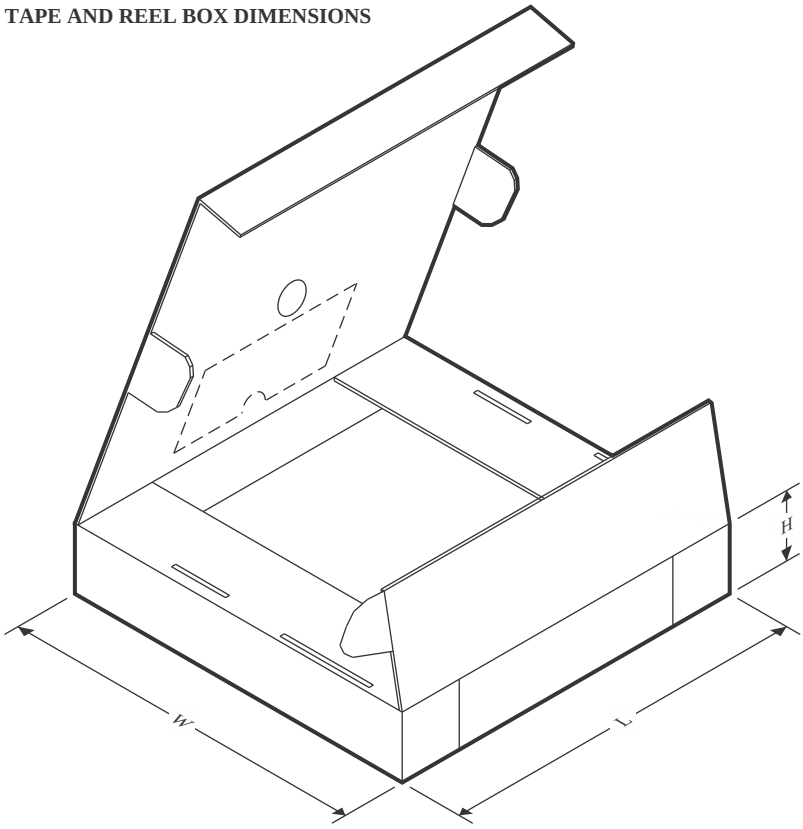
**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**




*All dimensions are nominal

| Device | Package Type | Package Drawing | Pins | SPQ | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
|---|---|---|---|---|---|---|---|---|---|---|---|---|
| TS5USBC410IYFFR | DSBGA | YFF | 12 | 3000 | 180.0 | 8.4 | 1.38 | 1.76 | 0.77 | 4.0 | 8.0 | Q2 |
| TS5USBC410IYFFR | DSBGA | YFF | 12 | 3000 | 180.0 | 8.4 | 1.38 | 1.76 | 0.77 | 4.0 | 8.0 | Q2 |
| TS5USBC410IYFFT | DSBGA | YFF | 12 | 250 | 180.0 | 8.4 | 1.38 | 1.76 | 0.77 | 4.0 | 8.0 | Q2 |
| TS5USBC410IYFFT | DSBGA | YFF | 12 | 250 | 180.0 | 8.4 | 1.38 | 1.76 | 0.77 | 4.0 | 8.0 | Q2 |
| TS5USBC410YFFR | DSBGA | YFF | 12 | 3000 | 180.0 | 8.4 | 1.38 | 1.76 | 0.77 | 4.0 | 8.0 | Q2 |
| TS5USBC410YFFT | DSBGA | YFF | 12 | 250 | 180.0 | 8.4 | 1.38 | 1.76 | 0.77 | 4.0 | 8.0 | Q2 |
| TS5USBC412IYFFR | DSBGA | YFF | 12 | 3000 | 180.0 | 8.4 | 1.38 | 1.76 | 0.77 | 4.0 | 8.0 | Q2 |
| TS5USBC412IYFFR | DSBGA | YFF | 12 | 3000 | 180.0 | 8.4 | 1.38 | 1.76 | 0.77 | 4.0 | 8.0 | Q2 |
| TS5USBC412IYFFT | DSBGA | YFF | 12 | 250 | 180.0 | 8.4 | 1.38 | 1.76 | 0.77 | 4.0 | 8.0 | Q2 |
| TS5USBC412IYFFT | DSBGA | YFF | 12 | 250 | 180.0 | 8.4 | 1.38 | 1.76 | 0.77 | 4.0 | 8.0 | Q2 |
| TS5USBC412YFFR | DSBGA | YFF | 12 | 3000 | 180.0 | 8.4 | 1.38 | 1.76 | 0.77 | 4.0 | 8.0 | Q2 |
| TS5USBC412YFFT | DSBGA | YFF | 12 | 250 | 180.0 | 8.4 | 1.38 | 1.76 | 0.77 | 4.0 | 8.0 | Q2 |

TAPE AND REEL BOX DIMENSIONS




*All dimensions are nominal

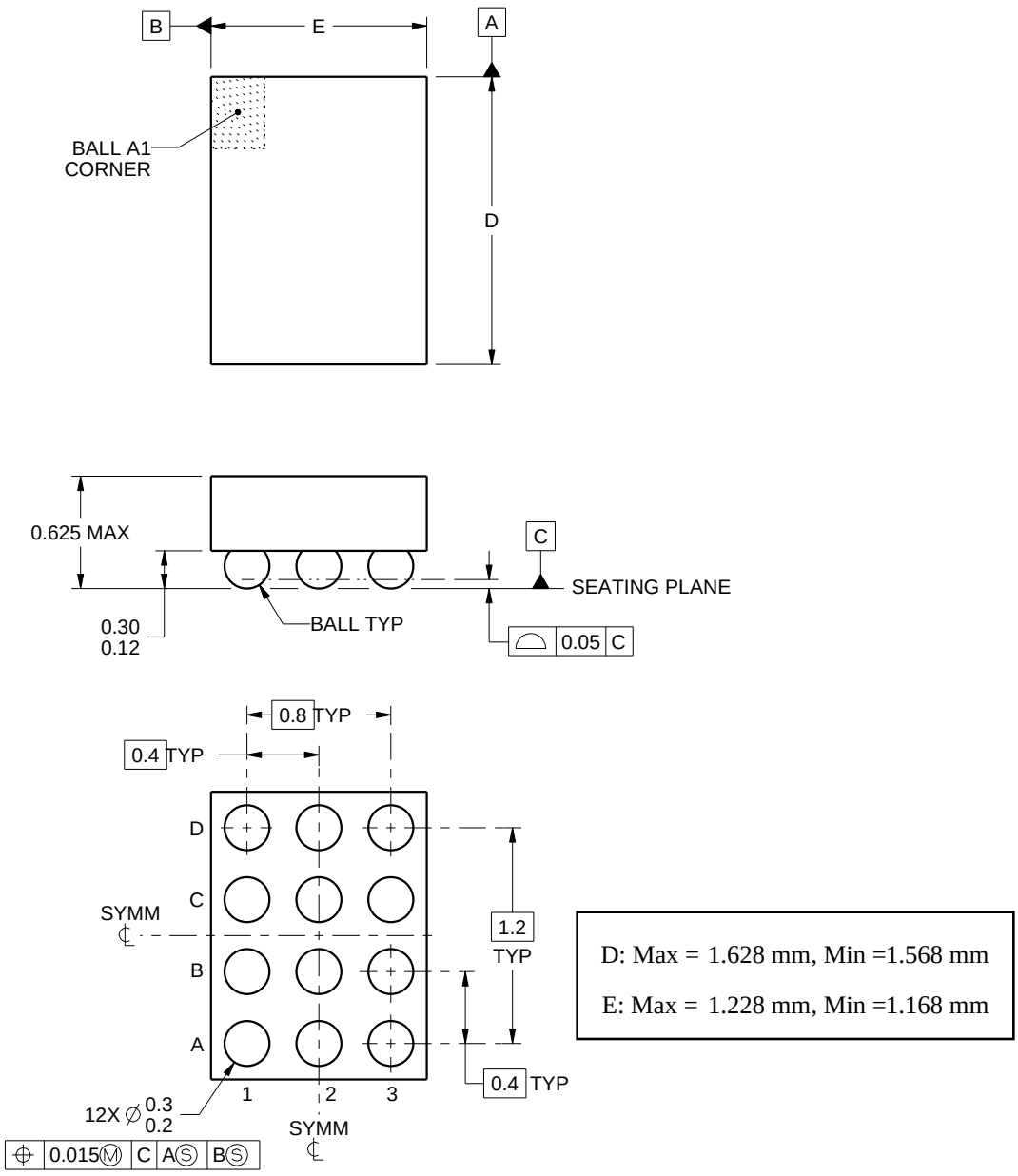
| Device | Package Type | Package Drawing | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) |
|---|---|---|---|---|---|---|---|
| TS5USBC410IYFFR | DSBGA | YFF | 12 | 3000 | 182.0 | 182.0 | 20.0 |
| TS5USBC410IYFFR | DSBGA | YFF | 12 | 3000 | 182.0 | 182.0 | 20.0 |
| TS5USBC410IYFFT | DSBGA | YFF | 12 | 250 | 182.0 | 182.0 | 20.0 |
| TS5USBC410IYFFT | DSBGA | YFF | 12 | 250 | 182.0 | 182.0 | 20.0 |
| TS5USBC410YFFR | DSBGA | YFF | 12 | 3000 | 182.0 | 182.0 | 20.0 |
| TS5USBC410YFFT | DSBGA | YFF | 12 | 250 | 182.0 | 182.0 | 20.0 |
| TS5USBC412IYFFR | DSBGA | YFF | 12 | 3000 | 182.0 | 182.0 | 20.0 |
| TS5USBC412IYFFR | DSBGA | YFF | 12 | 3000 | 182.0 | 182.0 | 20.0 |
| TS5USBC412IYFFT | DSBGA | YFF | 12 | 250 | 182.0 | 182.0 | 20.0 |
| TS5USBC412IYFFT | DSBGA | YFF | 12 | 250 | 182.0 | 182.0 | 20.0 |
| TS5USBC412YFFR | DSBGA | YFF | 12 | 3000 | 182.0 | 182.0 | 20.0 |
| TS5USBC412YFFT | DSBGA | YFF | 12 | 250 | 182.0 | 182.0 | 20.0 |

# PACKAGE OUTLINE

## YFF0012

## DSBGA - 0.625 mm max height

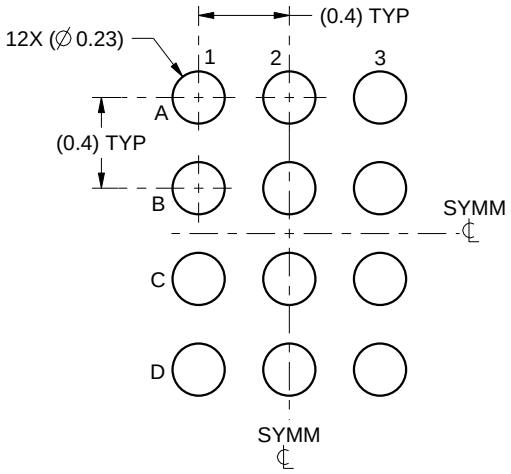
DIE SIZE BALL GRID ARRAY



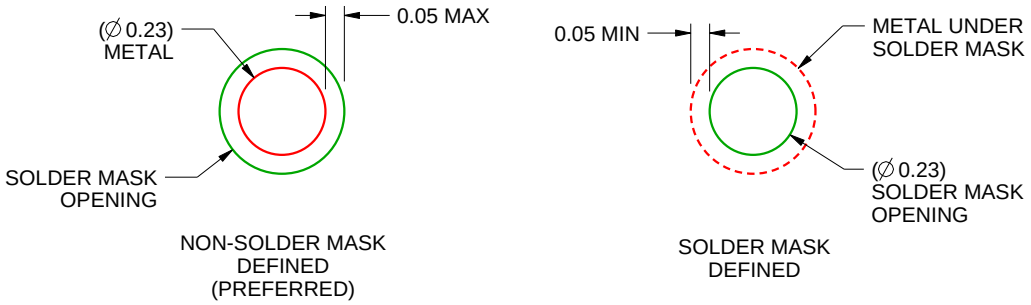

4222191/A 07/2015

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.




LAND PATTERN EXAMPLE
SCALE:30X

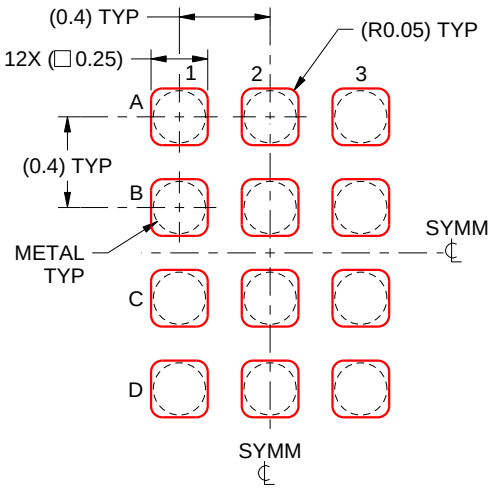



SOLDER MASK DETAILS
NOT TO SCALE

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NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).




SOLDER PASTE EXAMPLE
BASED ON 0.1 mm THICK STENCIL
SCALE:30X

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NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

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